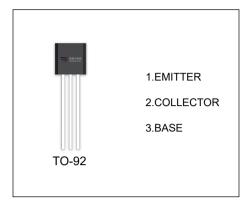


C945 TRANSISTOR (NPN)

FEATURE

- Excellent h_{FE} linearity
- Low noise
- Complementary to A733



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
C945	TO-92	Bulk	1000pcs/Bag
C945-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	150	mA
Pc	Collector Power Dissipation	400	mW
T_J , T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$



$T_a \text{=} 25\, ^{\circ}\text{C}\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =1mA , I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =100μA , I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100 μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =45V, I _B =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V ,I _C =0			0.1	μA
DO	h _{FE(1)}	V _{CE} =6V , I _C =1mA	70		700	
DC current gain	h _{FE(2)}	V _{CE} =6V , I _C =0.1mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA			1	V
Transition frequency	f _T	V _{CE} =6V,I _C =10mA,f=30MHz	200			MHz
Collector output capacitance	Cob	V _{CB} =10V,I _E =0,f=1MH _Z			3.0	pF
Noise figure	NF	VcE=6V,Ic=0.1mA		10		dB
Noise figure		R _G =10kΩ,f=1MHz		10		

CLASSIFICATION OF $h_{\text{FE}(1)}$

Rank	0	Y	GR	BL
Range	70-140	120-240	200-400	350-700



